

24th RD50 Workshop (Bucharest)

Thursday 12 June 2014

Session 3 - TCAD simulations (09:00 - 13:00)

-Conveners: Michael Moll

time	[id] title	presenter
09:00	[30] SiMS measurements & Simulation, Varied bias rail geometry structures characterization and TCAD simulation	GKOUKOUSIS, Vagelis
09:20	[20] A method to model the accumulation of oxide charge with fluence in an irradiated MSSD	PELTOLA, Timo Hannu Tapani
09:40	[26] Simulations of Hadron Irradiation Effects for Si Sensors Using Effective Bulk Damage Model	RANJEET, Ranjeet
10:00	[1] Trapping in p-on-n silicon sensors at fluences relevant for the HL-LHC	POEHLSEN, Thomas
10:30	Coffee	
11:00	[10] Lorentz angle measurement on ATLAS silicon microstrip sensors	YILDIRIM, Eda
11:20	[6] Edge-TCT studies of non-irradiated HVCMOS sensors	KRAMBERGER, Gregor
11:40	[35] Electric field measurement in irradiated silicon sensors by means of simulations and beam tests [Skype presentation]	Mr RUBINSKIY, Igor BOMBEN, Marco
12:00	[37] Impact of Low-Dose Electron Irradiation on the Charge Collection of n+p Silicon Strip Sensors	POEHLSEN, Thomas
12:20	[36] Discussion Session: Simulations and Sensor Characterizations	